

# LM3405A 1.6MHz, 1A Constant Current Buck LED Driver with Internal Compensation in Tiny SOT23 and eMSOP Package

Check for Samples: LM3405A

#### **FEATURES**

- V<sub>IN</sub> operating range of 3V to 22V
- Drives up to 5 High-Brightness LEDs in series at 1A
- Thin SOT23-6 package & eMSOP8 with exposed DAP
- 1.6MHz switching frequency
- EN/DIM input for enabling and PWM dimming of LEDs
- 300mΩ NMOS switch
- 40nA shutdown current at V<sub>IN</sub> = 5V
- · Internally compensated current-mode control
- Cycle-by-cycle current limit

- Input voltage UVLO
- Over-current protection
- Thermal shutdown

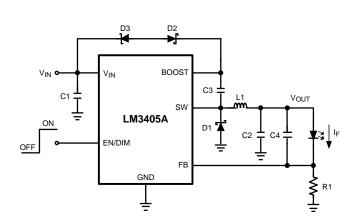
#### **APPLICATIONS**

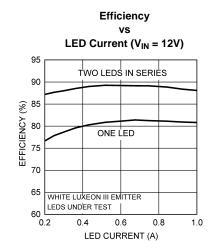
- LED Driver
- Constant Current Source
- Industrial Lighting
- LED Flashlights
- LED Lightbulbs

#### DESCRIPTION

The LM3405A is a 1A constant current buck LED driver designed to provide a simple, high efficiency solution for driving high power LEDs. With a 0.205V reference voltage feedback control to minimize power dissipation, an external resistor sets the current as needed for driving various types of LEDs. Switching frequency is internally set to 1.6MHz, allowing small surface mount inductors and capacitors to be used. The LM3405A utilizes current-mode control and internal compensation offering ease of use and predictable, high performance regulation over a wide range of operating conditions. With a maximum input voltage of 22V, it can drive up to 5 High-Brightness LEDs in series at 1A forward current, with the single LED forward voltage of approximately 3.7V. Additional features include user accessible EN/DIM pin for enabling and PWM dimming of LEDs, thermal shutdown, cycle-by-cycle current limit and over-current protection.

#### **Typical Application Circuit**





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# **Connection Diagram**

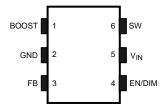


Figure 1. 6-Lead SOT-23 Package

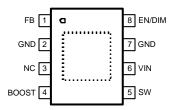


Figure 2. 8-Lead eMSOP Package

#### **SOT23-6 Pin Descriptions**

Pin(s)	Name	Application Information
1	BOOST	Boost voltage that drives the NMOS output switch. A bootstrap capacitor is connected between the BOOST and SW pins.
2	GND	Signal and power ground pin. Place the bottom resistor of the feedback network as close as possible to this pin.
3	FB	Feedback pin. Connect FB to external resistor divider to set output voltage.
4	EN/DIM	Enable control input. Logic high enables operation. Toggling this pin with a periodic logic square wave of varying duty cycle at different frequencies controls the brightness of LEDs. Do not allow this pin to float or be greater than $V_{\text{IN}} + 0.3V$ .
5	VIN	Input supply voltage. Connect a bypass capacitor locally from this pin to GND.
6	SW	Switch pin. Connect this pin to the inductor, catch diode, and bootstrap capacitor.

#### eMSOP8 Pin Descriptions

Pin	Name	Function
1	FB	Feedback pin. Connect FB to external resistor divider to set output voltage.
2, 7	GND	Signal and power ground pin. Place the bottom resistor of the feedback network as close as possible to this pin. Tie pins 2, 7 and DAP to one GND plane.
3	NC	No Connection
4	BOOST	Boost voltage that drives the NMOS output switch. A bootstrap capacitor is connected between the BOOST and SW pins.
5	SW	Switch pin. Connect this pin to the inductor, catch diode, and bootstrap capacitor.
6	VIN	Input supply voltage. Connect a bypass capacitor locally from this pin to GND.
8	EN/DIM	Enable control input. Logic high enables operation. Toggling this pin with a periodic logic square wave of varying duty cycle at different frequencies controls the brightness of LEDs. Do not allow this pin to float or be greater than $V_{\text{IN}}$ + 0.3V.
DAP		Attach to power ground pin



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

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# Absolute Maximum Ratings (1)

-0.5V to 24V
-0.5V to 24V
-0.5V to 30V
-0.5V to 6.0V
-0.5V to 3.0V
-0.5V to (V <sub>IN</sub> + 0.3V)
150°C
2kV
-65°C to +150°C
220°C

- (1) Absolute Maximum Ratings are limits beyond which damage to the device may occur. Operating Ratings define the conditions under which the device is intended to be functional. For guaranteed specifications and test conditions, see the Electrical Characteristics.
- (2) Human body model,  $1.5k\Omega$  in series with 100pF.

## Operating Ratings (1)

3V to 22V
-0.5V to (V <sub>IN</sub> + 0.3V)
2.5V to 5.5V
-40°C to +125°C
SOT23 118°C/W
eMSOP8 73°C/W
400mA
1A

- (1) Absolute Maximum Ratings are limits beyond which damage to the device may occur. Operating Ratings define the conditions under which the device is intended to be functional. For guaranteed specifications and test conditions, see the Electrical Characteristics.
- (2) Thermal shutdown will occur if the junction temperature (T<sub>J</sub>) exceeds 165°C. The maximum allowable power dissipation (P<sub>D</sub>) at any ambient temperature (T<sub>A</sub>) is P<sub>D</sub> = (T<sub>J(MAX)</sub> T<sub>A</sub>)/θ<sub>JA</sub>. This number applies to packages soldered directly onto a 3" x 3" PC board with 2oz. copper on 4 layers in still air. For a 2 layer board using 1 oz. copper in still air, θ<sub>JA</sub> = 204°C/W.
   (3) Thermal shutdown will occur if the junction temperature (T<sub>J</sub>) exceeds 165°C. The maximum allowable power dissipation (P<sub>D</sub>) at any
- (3) Thermal shutdown will occur if the junction temperature (T<sub>J</sub>) exceeds 165°C. The maximum allowable power dissipation (P<sub>D</sub>) at any ambient temperature (T<sub>A</sub>) is P<sub>D</sub> = (T<sub>J(MAX)</sub> T<sub>A</sub>)/θ<sub>JA</sub>. This number applies to packages soldered directly onto a 1" x 0.75" PC board with 1oz. copper on 4 layers in still air.



#### **Electrical Characteristics**

Unless otherwise specified,  $V_{IN}$  = 12V. Limits in standard type are for  $T_J$  = 25°C only; limits in **boldface type** apply over the junction temperature ( $T_J$ ) range of -40°C to +125°C. Minimum and Maximum limits are guaranteed through test, design, or statistical correlation. Typical values represent the most likely parametric norm, and are provided for reference purposes only.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
$V_{FB}$	Feedback Voltage		0.188	0.205	0.220	V
$\Delta V_{FB}/(\Delta V_{IN}xV_{FB})$	Feedback Voltage Line Regulation	V <sub>IN</sub> = 3V to 22V		0.01		%/V
I <sub>FB</sub>	Feedback Input Bias Current	Sink/Source		10	250	nA
	Under-voltage Lockout	V <sub>IN</sub> Rising		2.74	2.95	٧
UVLO	Under-voltage Lockout	V <sub>IN</sub> Falling	1.9	2.3		V
	UVLO Hysteresis			0.44		V
f <sub>SW</sub>	Switching Frequency		1.2	1.6	1.9	MHz
D <sub>MAX</sub>	Maximum Duty Cycle	V <sub>FB</sub> = 0V	85	94		%
Б	Cuitab ON Basistanas	SOT23 ( $V_{BOOST} - V_{SW} = 3V$ )		300	600	0
R <sub>DS(ON)</sub>	Switch ON Resistance	eMSOP (V <sub>BOOST</sub> - V <sub>SW</sub> = 3V)		360	700	mΩ
I <sub>CL</sub>	Switch Current Limit	$V_{BOOST}$ - $V_{SW}$ = 3V, $V_{IN}$ = 3V	1.2	2.0	2.8	Α
	Quiescent Current	Switching, V <sub>FB</sub> = 0.195V		1.8	2.8	mA
lα	Quiescent Current (Shutdown)	$V_{EN/DIM} = 0V$		0.3		μΑ
V	Enable Threshold Voltage	V <sub>EN/DIM</sub> Rising	1.8			٧
$V_{EN/DIM\_TH}$	Shutdown Threshold Voltage	V <sub>EN/DIM</sub> Falling			0.4	V
I <sub>EN/DIM</sub>	EN/DIM Pin Current	Sink/Source		0.01		μΑ
I <sub>SW</sub>	Switch Leakage	V <sub>IN</sub> = 22V		0.1		μΑ

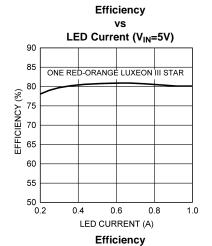
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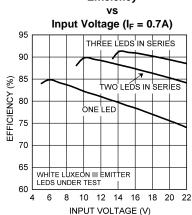
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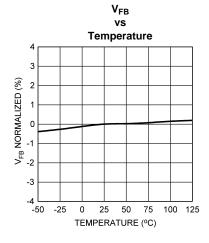


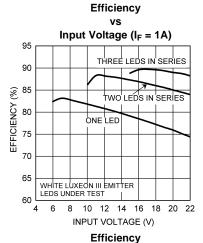
## **Typical Performance Characteristics**

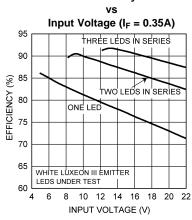
Unless otherwise specified,  $V_{IN}$  = 12V,  $V_{BOOST}$  -  $V_{SW}$  = 5V and  $T_A$  = 25°C.

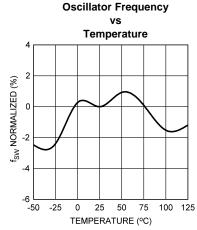










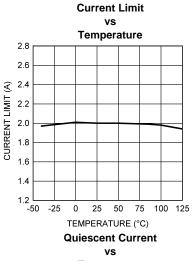


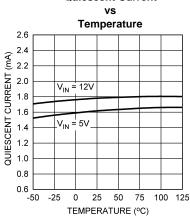
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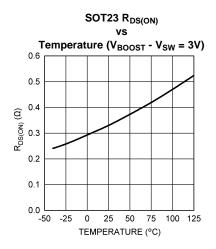


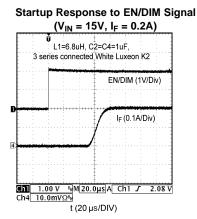
## **Typical Performance Characteristics (continued)**

Unless otherwise specified,  $V_{IN}$  = 12V,  $V_{BOOST}$  -  $V_{SW}$  = 5V and  $T_A$  = 25°C.









#### **BLOCK DIAGRAM**

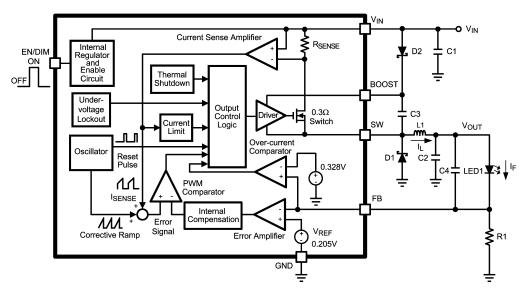


Figure 3. Simplified Block Diagram

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#### **APPLICATION INFORMATION**

#### THEORY OF OPERATION

The LM3405A is a PWM, current-mode controlled buck switching regulator designed to provide a simple, high efficiency solution for driving LEDs with a preset switching frequency of 1.6MHz. This high frequency allows the LM3405A to operate with small surface mount capacitors and inductors, resulting in LED drivers that need only a minimum amount of board space. The LM3405A is internally compensated, simple to use, and requires few external components.

The following description of operation of the LM3405A will refer to the Simplified Block Diagram (Figure 3) and to the waveforms in Figure 4. The LM3405A supplies a regulated output current by switching the internal NMOS power switch at constant frequency and variable duty cycle. A switching cycle begins at the falling edge of the reset pulse generated by the internal oscillator. When this pulse goes low, the output control logic turns on the internal NMOS power switch. During this on-time, the SW pin voltage ( $V_{SW}$ ) swings up to approximately  $V_{IN}$ , and the inductor current ( $I_L$ ) increases with a linear slope.  $I_L$  is measured by the current sense amplifier, which generates an output proportional to the switch current. The sense signal is summed with the regulator's corrective ramp and compared to the error amplifier's output, which is proportional to the difference between the feedback voltage and  $V_{REF}$ . When the PWM comparator output goes high, the internal power switch turns off until the next switching cycle begins. During the switch off-time, inductor current discharges through the catch diode D1, which forces the SW pin to swing below ground by the forward voltage ( $V_{D1}$ ) of the catch diode. The regulator loop adjusts the duty cycle (D) to maintain a constant output current ( $I_F$ ) through the LED, by forcing FB pin voltage to be equal to  $V_{REF}$  (0.205V).

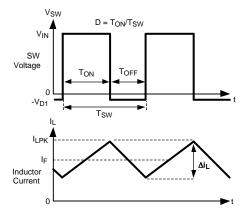


Figure 4. SW Pin Voltage and Inductor Current Waveforms of LM3405A

#### **BOOST FUNCTION**

Capacitor C3 and diode D2 in Figure 3 are used to generate a voltage  $V_{BOOST}$ . The voltage across C3,  $V_{BOOST}$  -  $V_{SW}$ , is the gate drive voltage to the internal NMOS power switch. To properly drive the internal NMOS switch during its on-time,  $V_{BOOST}$  needs to be at least 2.5V greater than  $V_{SW}$ . A large value of  $V_{BOOST}$  -  $V_{SW}$  is recommended to achieve better efficiency by minimizing both the internal switch ON resistance ( $R_{DS(ON)}$ ), and the switch rise and fall times. However,  $V_{BOOST}$  -  $V_{SW}$  should not exceed the maximum operating limit of 5.5V.

When the LM3405A starts up, internal circuitry from  $V_{IN}$  supplies a 20mA current to the BOOST pin, flowing out of the BOOST pin into C3. This current charges C3 to a voltage sufficient to turn the switch on. The BOOST pin will continue to source current to C3 until the voltage at the feedback pin is greater than 123mV.

There are various methods to derive V<sub>BOOST</sub>:

- 1. From the input voltage (V<sub>IN</sub>)
- 2. From the output voltage (V<sub>OUT</sub>)
- 3. From a shunt or series zener diode
- From an external distributed voltage rail (V<sub>EXT</sub>)



The first method is shown in the Simplified Block Diagram of Figure 3. Capacitor C3 is charged via diode D2 by  $V_{IN}$ . During a normal switching cycle, when the internal NMOS power switch is off ( $T_{OFF}$ ) (refer to Figure 4),  $V_{BOOST}$  equals  $V_{IN}$  minus the forward voltage of D2 ( $V_{D2}$ ), during which the current in the inductor (L1) forward biases the catch diode D1 ( $V_{D1}$ ). Therefore the gate drive voltage stored across C3 is:

$$V_{BOOST} - V_{SW} = V_{IN} - V_{D2} + V_{D1}$$
 (1)

When the NMOS switch turns on  $(T_{ON})$ , the switch pin rises to:

$$V_{SW} = V_{IN} - (R_{DS(ON)} \times I_L)$$
 (2)

Since the voltage across C3 remains unchanged,  $V_{BOOST}$  is forced to rise thus reverse biasing D2. The voltage at  $V_{BOOST}$  is then:

$$V_{BOOST} = 2V_{IN} - (R_{DS(ON)} \times I_L) - V_{D2} + V_{D1}$$
(3)

Depending on the quality of the diodes D1 and D2, the gate drive voltage in this method can be slightly less or larger than the input voltage  $V_{IN}$ . For best performance, ensure that the variation of the input supply does not cause the gate drive voltage to fall outside the recommended range:

$$2.5V < V_{\text{IN}} - V_{D2} + V_{D1} < 5.5V \tag{4}$$

The second method for deriving the boost voltage is to connect D2 to the output as shown in Figure 5. The gate drive voltage in this configuration is:

$$V_{BOOST} - V_{SW} = V_{OUT} - V_{D2} + V_{D1}$$
 (5)

Since the gate drive voltage needs to be in the range of 2.5V to 5.5V, the output voltage  $V_{OUT}$  should be limited to a certain range. For the calculation of  $V_{OUT}$ , see OUTPUT VOLTAGE section.

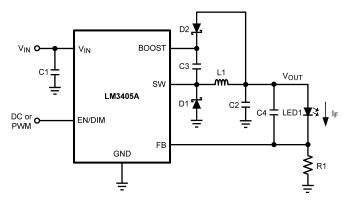


Figure 5. V<sub>BOOST</sub> derived from V<sub>OUT</sub>

The third method can be used in the applications where both  $V_{IN}$  and  $V_{OUT}$  are greater than 5.5V. In these cases, C3 cannot be charged directly from these voltages; instead C3 can be charged from  $V_{IN}$  or  $V_{OUT}$  minus a zener voltage ( $V_{D3}$ ) by placing a zener diode D3 in series with D2 as shown in Figure 6. When using a series zener diode from the input, the gate drive voltage is  $V_{IN} - V_{D3} - V_{D2} + V_{D1}$ .

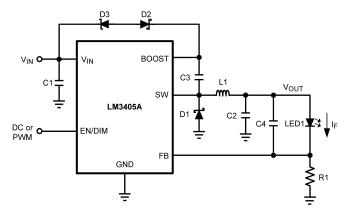


Figure 6. V<sub>BOOST</sub> derived from V<sub>IN</sub> through a Series Zener



An alternate method is to place the zener diode D3 in a shunt configuration as shown in Figure 7. A small 350mW to 500mW, 5.1V zener in a SOT-23 or SOD package can be used for this purpose. A small ceramic capacitor such as a 6.3V,  $0.1\mu F$  capacitor (C5) should be placed in parallel with the zener diode. When the internal NMOS switch turns on, a pulse of current is drawn to charge the internal NMOS gate capacitance. The  $0.1\mu F$  parallel shunt capacitor ensures that the  $V_{BOOST}$  voltage is maintained during this time. Resistor R2 should be chosen to provide enough RMS current to the zener diode and to the BOOST pin. A recommended choice for the zener current ( $I_{ZENER}$ ) is 1mA. The current  $I_{BOOST}$  into the BOOST pin supplies the gate current of the NMOS power switch. It reaches a maximum of around 3.6mA at the highest gate drive voltage of 5.5V over the LM3405A operating range.

For the worst case I<sub>BOOST</sub>, increase the current by 50%. In that case, the maximum boost current will be:

$$I_{BOOST-MAX} = 1.5 \times 3.6 \text{mA} = 5.4 \text{mA}$$
 (6)

R2 will then be given by:

$$R2 = (V_{IN} - V_{ZENER}) / (I_{BOOST\_MAX} + I_{ZENER})$$
(7)

For example, let  $V_{IN} = 12V$ ,  $V_{ZENER} = 5V$ ,  $I_{ZENER} = 1mA$ , then:

$$R2 = (12V - 5V) / (5.4mA + 1mA) = 1.09k\Omega$$
 (8)

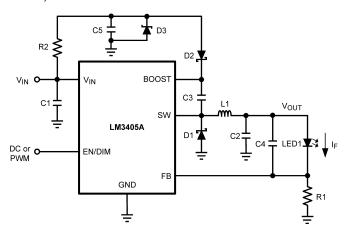


Figure 7. V<sub>BOOST</sub> derived from V<sub>IN</sub> through a Shunt Zener

The fourth method can be used in an application which has an external low voltage rail,  $V_{EXT}$ . C3 can be charged through D2 from  $V_{EXT}$ , independent of  $V_{IN}$  and  $V_{OUT}$  voltage levels. Again for best performance, ensure that the gate drive voltage,  $V_{EXT}$  -  $V_{D2}$  +  $V_{D1}$ , falls in the range of 2.5V to 5.5V.

#### **SETTING THE LED CURRENT**

LM3405A is a constant current buck regulator. The LEDs are connected between  $V_{OUT}$  and the FB pin as shown in the Typical Application Circuit. The FB pin is at 0.205V in regulation and therefore the LED current  $I_F$  is set by  $V_{FB}$  and resistor R1 from FB to ground by the following equation:

$$I_{F} = V_{FB} / R1 \tag{9}$$

 $I_F$  should not exceed the 1A current capability of LM3405A and therefore R1 minimum must be approximately  $0.2\Omega$ .  $I_F$  should also be kept above 200mA for stable operation, and therefore R1 maximum must be approximately  $1\Omega$ . If average LED currents less than 200mA are desired, the EN/DIM pin can be used for PWM dimming. See LED PWM DIMMING section.

#### **OUTPUT VOLTAGE**

The output voltage is primarily determined by the number of LEDs (n) connected from  $V_{OUT}$  to FB pin and therefore  $V_{OUT}$  can be written as :

$$V_{OUT} = ((n \times V_F) + V_{FB})$$
 (10)

where V<sub>F</sub> is the forward voltage of one LED at the set LED current level (see LED manufacturer datasheet for forward characteristics curve).



#### **ENABLE MODE / SHUTDOWN MODE**

The LM3405A has both enable and shutdown modes that are controlled by the EN/DIM pin. Connecting a voltage source greater than 1.8V to the EN/DIM pin enables the operation of LM3405A, while reducing this voltage below 0.4V places the part in a low quiescent current (0.3 $\mu$ A typical) shutdown mode. There is no internal pull-up on EN/DIM pin, therefore an external signal is required to initiate switching. Do not allow this pin to float or rise to 0.3V above V<sub>IN</sub>. It should be noted that when the EN/DIM pin voltage rises above 1.8V while the input voltage is greater than UVLO, there is a finite delay before switching starts. During this delay the LM3405A will go through a power on reset state after which the internal soft-start process commences. The soft-start process limits the inrush current and brings up the LED current (I<sub>F</sub>) in a smooth and controlled fashion. The total combined duration of the power on reset delay, soft-start delay and the delay to fully establish the LED current is in the order of 100 $\mu$ s (refer to Figure 12).

The simplest way to enable the operation of LM3405A is to connect the EN/DIM pin to  $V_{IN}$  which allows self start-up of LM3405A whenever the input voltage is applied. However, when an input voltage of slow rise time is used to power the application and if both the input voltage and the output voltage are not fully established before the soft-start time elapses, the control circuit will command maximum duty cycle operation of the internal power switch to bring up the output voltage rapidly. When the feedback pin voltage exceeds 0.205V, the duty cycle will have to reduce from the maximum value accordingly, to maintain regulation. It takes a finite amount of time for this reduction of duty cycle and this will result in a spike in LED current for a short duration as shown in Figure 8. In applications where this LED current overshoot is undesirable, EN/DIM pin voltage can be separately applied and delayed such that  $V_{IN}$  is fully established before the EN/DIM pin voltage reaches the enable threshold. The effect of delaying EN/DIM with respect to  $V_{IN}$  on the LED current is shown in Figure 9. For a fast rising input voltage (200µs for example), there is no need to delay the EN/DIM signal since soft-start can smoothly bring up the LED current as shown in Figure 10.

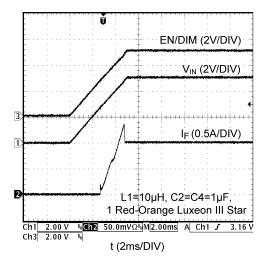


Figure 8. Startup Response to VIN with 5ms rise time

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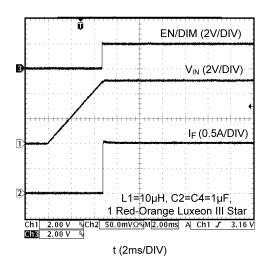


Figure 9. Startup Response to VIN with EN/DIM delayed

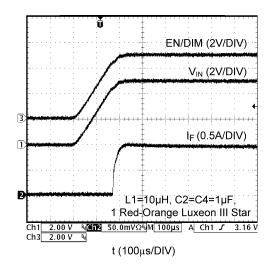


Figure 10. Startup Response to V<sub>IN</sub> with 200µs rise time

#### **LED PWM DIMMING**

The LED brightness can be controlled by applying a periodic pulse signal to the EN/DIM pin and varying its frequency and/or duty cycle. This so-called PWM dimming method controls the average light output by pulsing the LED current between the set value and zero. A logic high level at the EN/DIM pin turns on the LED current whereas a logic low level turns off the LED current. Figure 11 shows a typical LED current waveform in PWM dimming mode. As explained in the previous section, there is approximately a 100µs delay from the EN/DIM signal going high to fully establishing the LED current as shown in Figure 12. This 100µs delay sets a maximum frequency limit for the driving signal that can be applied to the EN/DIM pin for PWM dimming. Figure 13 shows the average LED current versus duty cycle of PWM dimming signal for various frequencies. The applicable frequency range to drive LM3405A for PWM dimming is from 100Hz to 5kHz. The dimming ratio reduces drastically when the applied PWM dimming frequency is greater than 5kHz.



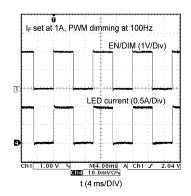


Figure 11. PWM Dimming of LEDs using the EN/DIM Pin

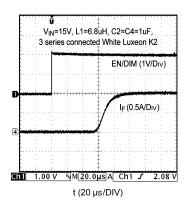


Figure 12. Startup Response to EN/DIM with  $I_F = 1A$ 

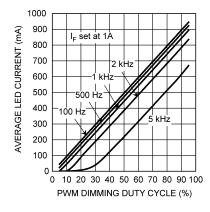


Figure 13. Average LED Current versus Duty Cycle of PWM Dimming Signal at EN/DIM Pin

#### **UNDER-VOLTAGE LOCKOUT**

Under-voltage lockout (UVLO) prevents the LM3405A from operating until the input voltage exceeds 2.74V (typical). The UVLO threshold has approximately 440mV of hysteresis, so the part will operate until  $V_{\text{IN}}$  drops below 2.3V (typical). Hysteresis prevents the part from turning off during power up if  $V_{\text{IN}}$  is non-monotonic.

#### **CURRENT LIMIT**

The LM3405A uses cycle-by-cycle current limit to protect the internal power switch. During each switching cycle, a current limit comparator detects if the power switch current exceeds 2.0A (typical), and turns off the switch until the next switching cycle begins.



#### **OVER-CURRENT PROTECTION**

The LM3405A has a built in over-current comparator that compares the FB pin voltage to a threshold voltage that is 60% higher than the internal reference  $V_{REF}$ . Once the FB pin voltage exceeds this threshold level (typically 328mV), the internal NMOS power switch is turned off, which allows the feedback voltage to decrease towards regulation. This threshold provides an upper limit for the LED current. LED current overshoot is limited to 328mV/R1 by this comparator during transients.

#### THERMAL SHUTDOWN

Thermal shutdown limits total power dissipation by turning off the internal power switch when the IC junction temperature exceeds 165°C. After thermal shutdown occurs, the power switch does not turn on until the junction temperature drops below approximately 150°C.

#### **Design Guide**

#### **INDUCTOR (L1)**

The Duty Cycle (D) can be approximated quickly using the ratio of output voltage ( $V_{OUT}$ ) to input voltage ( $V_{IN}$ ):

$$D = \frac{v_{OUT}}{V_{IN}} \tag{11}$$

The catch diode (D1) forward voltage drop and the voltage drop across the internal NMOS must be included to calculate a more accurate duty cycle. Calculate D by using the following formula:

$$D = \frac{V_{OUT} + V_{D1}}{V_{IN} + V_{D1} - V_{SW}}$$
 (12)

V<sub>SW</sub> can be approximated by:

$$V_{SW} = I_F x R_{DS(ON)}$$
 (13)

The diode forward drop  $(V_{D1})$  can range from 0.3V to 0.7V depending on the quality of the diode. The lower  $V_{D1}$  is, the higher the operating efficiency of the converter.

The inductor value determines the output ripple current ( $\Delta i_L$ , as defined in Figure 4). Lower inductor values decrease the size of the inductor, but increases the output ripple current. An increase in the inductor value will decrease the output ripple current. The ratio of ripple current to LED current is optimized when it is set between 0.3 and 0.4 at 1A LED current. This ratio r is defined as:

$$r = \frac{\Delta i_L}{l_F} \tag{14}$$

One must also ensure that the minimum current limit (1.2A) is not exceeded, so the peak current in the inductor must be calculated. The peak current  $(I_{LPK})$  in the inductor is calculated as:

$$I_{LPK} = I_F + \Delta i_L/2 \tag{15}$$

When the designed maximum output current is reduced, the ratio r can be increased. At a current of 0.2A, r can be made as high as 0.7. The ripple ratio can be increased at lighter loads because the net ripple is actually quite low, and if r remains constant the inductor value can be made quite large. An equation empirically developed for the maximum ripple ratio at any current below 2A is:

$$r = 0.387 \text{ x } I_{OUT}^{-0.3667}$$
 (16)

Note that this is just a guideline.

The LM3405A operates at a high frequency allowing the use of ceramic output capacitors without compromising transient response. Ceramic capacitors allow higher inductor ripple without significantly increasing LED current ripple. See the output capacitor and feed-forward capacitor sections for more details on LED current ripple.

Now that the ripple current or ripple ratio is determined, the inductance is calculated by:

$$L = \frac{V_{OUT} + V_{D1}}{I_F \times r \times f_{SW}} \times (1-D)$$
 (17)



where  $f_{SW}$  is the switching frequency and  $I_F$  is the LED current. When selecting an inductor, make sure that it is capable of supporting the peak output current without saturating. Inductor saturation will result in a sudden reduction in inductance and prevent the regulator from operating correctly. Because of the operating frequency of the LM3405A, ferrite based inductors are preferred to minimize core losses. This presents little restriction since the variety of ferrite based inductors is huge. Lastly, inductors with lower series resistance (DCR) will provide better operating efficiency. For recommended inductor selection, refer to Circuit Examples and Recommended Inductance Range in Table 1.

**Inductance Range and Inductor Current Ripple** ΙF 6.8µH-15µH 1.0A Inductance 6.8µH 10µH 15µH 36% 24%  $\Delta i_L / I_F^*$ 51% 10µH-22µH 0.6A Inductance 10µH 15µH 22µH 58%  $\Delta i_L / I_F^*$ 39% 26% 15μΗ-27μΗ 0.2A Inductance 15µH 22µH 27µH 79%  $\Delta i_L / I_F^*$ 116% 65%

**Table 1. Recommended Inductance Range** 

#### **INPUT CAPACITOR (C1)**

An input capacitor is necessary to ensure that  $V_{IN}$  does not drop excessively during switching transients. The primary specifications of the input capacitor are capacitance, voltage rating, RMS current rating, and ESL (Equivalent Series Inductance). The input voltage rating is specifically stated by the capacitor manufacturer. Make sure to check any recommended deratings and also verify if there is any significant change in capacitance at the operating input voltage and the operating temperature. The input capacitor maximum RMS input current rating ( $I_{RMS-IN}$ ) must be greater than:

$$I_{RMS-IN} = I_F \times \sqrt{D \times \left(1 - D + \frac{r^2}{12}\right)}$$
 (18)

It can be shown from the above equation that maximum RMS capacitor current occurs when D = 0.5. Always calculate the RMS at the point where the duty cycle D, is closest to 0.5. The ESL of an input capacitor is usually determined by the effective cross sectional area of the current path. A large leaded capacitor will have high ESL and an 0805 ceramic chip capacitor will have very low ESL. At the operating frequency of the LM3405A, certain capacitors may have an ESL so large that the resulting inductive impedance ( $2\pi fL$ ) will be higher than that required to provide stable operation. It is strongly recommended to use ceramic capacitors due to their low ESR and low ESL. A  $10\mu F$  multilayer ceramic capacitor (MLCC) is a good choice for most applications. In cases where large capacitance is required, use surface mount capacitors such as Tantalum capacitors and place at least a  $1\mu F$  ceramic capacitor close to the  $V_{IN}$  pin. For MLCCs it is recommended to use X7R or X5R dielectrics. Consult capacitor manufacturer datasheet to see how rated capacitance varies over operating conditions.

#### **OUTPUT CAPACITOR (C2)**

The output capacitor is selected based upon the desired reduction in LED current ripple. A  $1\mu F$  ceramic capacitor results in very low LED current ripple for most applications. Due to the high switching frequency, the  $1\mu F$  capacitor alone (without feed-forward capacitor C4) can filter more than 90% of the inductor current ripple for most applications where the sum of LED dynamic resistance and R1 is larger than  $1\Omega$ . Since the internal compensation is tailored for small output capacitance with very low ESR, it is strongly recommended to use a ceramic capacitor with capacitance less than  $3.3\mu F$ .

Given the availability and quality of MLCCs and the expected output voltage of designs using the LM3405A, there is really no need to review other capacitor technologies. A benefit of ceramic capacitors is their ability to bypass high frequency noise. A certain amount of switching edge noise will couple through the parasitic capacitances in the inductor to the output. A ceramic capacitor will bypass this noise. In cases where large capacitance is required, use Electrolytic or Tantalum capacitors with large ESR, and verify the loop performance on the bench. Like the input capacitor, multilayer ceramic capacitors are recommended X7R or X5R. Again, verify actual capacitance at the desired operating voltage and temperature.



Check the RMS current rating of the capacitor. The maximum RMS current rating of the capacitor is:

$$I_{RMS-OUT} = I_F \times \frac{r}{\sqrt{12}}$$
 (19)

One may select a 1206 size ceramic capacitor for C2 since its current rating is typically higher than 1A, more than enough for the requirement.

#### **FEED-FORWARD CAPACITOR (C4)**

The feed-forward capacitor (designated as C4) connected in parallel with the LED string is required to provide multiple benefits to the LED driver design. It greatly improves the large signal transient response and suppresses LED current overshoot that may otherwise occur during PWM dimming; it also helps to shape the rise and fall times of the LED current pulse during PWM dimming thus reducing EMI emission; it reduces LED current ripple by bypassing some of inductor ripple from flowing through the LED. For most applications, a  $1\mu F$  ceramic capacitor is sufficient. In fact, the combination of a  $1\mu F$  feed-forward ceramic capacitor and a  $1\mu F$  output ceramic capacitor leads to less than 1% current ripple flowing through the LED. Lower and higher C4 values can be used, but bench validation is required to ensure the performance meets the application requirement.

Figure 14 shows a typical LED current waveform during PWM dimming without feed-forward capacitor. At the beginning of each PWM cycle, overshoot can be seen in the LED current. Adding a 1µF feed-forward capacitor can totally remove the overshoot as shown in Figure 15.

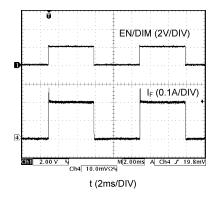


Figure 14. PWM Dimming without Feed-Forward Capacitor

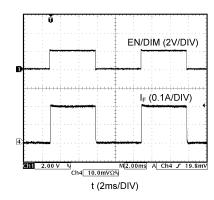


Figure 15. PWM Dimming with a 1µF Feed-Forward Capacitor

#### **CATCH DIODE (D1)**

The catch diode (D1) conducts during the switch off-time. A Schottky diode is required for its fast switching time and low forward voltage drop. The catch diode should be chosen such that its current rating is greater than:

$$I_{D1} = I_F \times (1-D)$$
 (20)

The reverse breakdown rating of the diode must be at least the maximum input voltage plus appropriate margin. To improve efficiency, choose a Schottky diode with a low forward voltage drop.



#### **BOOST DIODE (D2)**

A standard diode such as the 1N4148 type is recommended. For  $V_{\mathsf{BOOST}}$  circuits derived from voltages less than 3.3V, a small-signal Schottky diode is recommended for better efficiency. A good choice is the BAT54 small signal diode.

#### **BOOST CAPACITOR (C3)**

A 0.01µF ceramic capacitor with a voltage rating of at least 6.3V is sufficient. The X7R and X5R MLCCs provide the best performance.

#### POWER LOSS ESTIMATION

The main power loss in LM3405A includes three basic types of loss in the internal power switch: conduction loss, switching loss, and gate charge loss. In addition, there is loss associated with the power required for the internal circuitry of IC.

The conduction loss is calculated as:

$$P_{COND} = (I_F^2 \times D) \times \left(1 + \frac{1}{3} \times \left(\frac{\Delta i_L}{I_F}\right)^2\right) \times R_{DS(ON)}$$
(21)

If the inductor ripple current is fairly small (for example, less than 40%), the conduction loss can be simplified to:

$$P_{COND} = I_F^2 \times R_{DS(ON)} \times D \tag{22}$$

The switching loss occurs during the switch on and off transition periods, where voltage and current overlap resulting in power loss. The simplest means to determine this loss is to empirically measure the rise and fall times (10% to 90%) of the voltage at the switch pin.

Switching power loss is calculated as follows:

$$P_{SW} = 0.5 \times V_{IN} \times I_F \times f_{SW} \times (T_{RISE} + T_{FALL})$$
 (23)

The gate charge loss is associated with the gate charge Q<sub>G</sub> required to drive the switch:

$$P_{G} = f_{SW} \times V_{IN} \times Q_{G} \tag{24}$$

The power loss required for operation of the internal circuitry:

$$P_{Q} = I_{Q} \times V_{IN} \tag{25}$$

I<sub>O</sub> is the quiescent operating current, and is typically around 1.8mA for the LM3405A.

The total power loss in the IC is:

$$P_{\text{INTERNAL}} = P_{\text{COND}} + P_{\text{SW}} + P_{\text{G}} + P_{\text{Q}} \tag{26}$$

An example of power losses for a typical application is shown in Table 2:

#### **Table 2. Power Loss Tabulation**

Cond	Conditions		er loss
V <sub>IN</sub>	12V		
V <sub>OUT</sub>	3.9V		
Гоит	1.0A		
V <sub>D1</sub>	0.45V		
R <sub>DS(ON)</sub>	$300 m\Omega$	P <sub>COND</sub>	108mW
f <sub>SW</sub>	1.6MHz		
T <sub>RISE</sub>	18ns	D	288mW
T <sub>FALL</sub>	12ns	P <sub>SW</sub>	20011100
IQ	1.8mA	$P_{Q}$	22mW
$Q_{G}$	1.4nC	$P_{G}$	27mW
D is calculated to be 0.36		·	



$$\Sigma \left( P_{COND} + P_{SW} + P_{Q} + P_{G} \right) = P_{INTERNAL} \tag{27}$$

$$P_{\rm INTERNAL} = 445 \, \rm mW \tag{28}$$

#### **PCB Layout Considerations**

When planning the layout there are a few things to consider when trying to achieve a clean, regulated output. The most important consideration when completing the layout is the close coupling of the GND connections of the input capacitor C1 and the catch diode D1. These ground ends should be close to one another and be connected to the GND plane with at least two through-holes. Place these components as close to the IC as possible. The next consideration is the location of the GND connection of the output capacitor C2, which should be near the GND connections of C1 and D1.

There should be a continuous ground plane on the bottom layer of a two-layer board except under the switching node island.

The FB pin is a high impedance node and care should be taken to make the FB trace short to avoid noise pickup that causes inaccurate regulation. The LED current setting resistor R1 should be placed as close as possible to the IC, with the GND of R1 placed as close as possible to the GND of the IC. The V<sub>OUT</sub> trace to LED anode should be routed away from the inductor and any other traces that are switching.

High AC currents flow through the  $V_{IN}$ , SW and  $V_{OUT}$  traces, so they should be as short and wide as possible. Radiated noise can be decreased by choosing a shielded inductor.

The remaining components should also be placed as close as possible to the IC. Please see Application Note AN-1229 for further considerations and the LM3405A demo board as an example of a four-layer layout.

#### LM3405A Circuit Examples

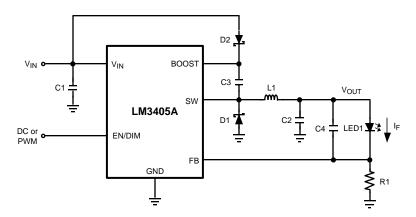


Figure 16.  $V_{BOOST}$  derived from  $V_{IN}$  ( $V_{IN} = 5V$ ,  $I_F = 1A$ )

Table 3. Bill of Materials for Figure 16

Part Value	Part Number	Manufacturer		
1A LED Driver	LM3405A	National Semiconductor		
10μF, 6.3V, X5R	C3216X5R0J106M	TDK		
1μF, 10V, X7R	GRM319R71A105KC01D	Murata		
0.01µF, 16V, X7R	0805YC103KAT2A	AVX		
1μF, 10V, X7R	GRM319R71A105KC01D	Murata		
Schottky, 0.37V at 1A, V <sub>R</sub> = 10V	MBRM110LT1G	ON Semiconductor		
Schottky, 0.36V at 15mA	CMDSH-3	Central Semiconductor		
4.7μH, 1.6A	SLF6028T-4R7M1R6	TDK		
0.2Ω, 0.5W, 1%	WSL2010R2000FEA	Vishay		
1.5A, White LED	LXK2-PW14	Lumileds		
	1A LED Driver  10μF, 6.3V, X5R  1μF, 10V, X7R  0.01μF, 16V, X7R  1μF, 10V, X7R  Schottky, 0.37V at 1A, $V_R = 10V$ Schottky, 0.36V at 15mA  4.7μH, 1.6A  0.2 $\Omega$ , 0.5W, 1%	1A LED Driver       LM3405A $10\mu\text{F}$ , 6.3V, X5R       C3216X5R0J106M $1\mu\text{F}$ , 10V, X7R       GRM319R71A105KC01D $0.01\mu\text{F}$ , 16V, X7R       0805YC103KAT2A $1\mu\text{F}$ , 10V, X7R       GRM319R71A105KC01D         Schottky, 0.37V at 1A, $V_R = 10V$ MBRM110LT1G         Schottky, 0.36V at 15mA       CMDSH-3 $4.7\mu\text{H}$ , 1.6A       SLF6028T-4R7M1R6 $0.2\Omega$ , 0.5W, 1%       WSL2010R2000FEA		



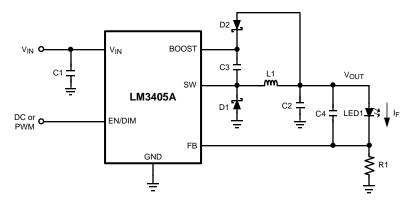


Figure 17.  $V_{BOOST}$  derived from  $V_{OUT}$  (  $V_{IN}$  = 12V,  $I_F$  = 1A )

Table 4. Bill of Materials for Figure 17

Part ID	Part Value	Part Number	Manufacturer
U1	1A LED Driver	LM3405A	National Semiconductor
C1, Input Cap	10μF, 25V, X5R	ECJ-3YB1E106K	Panasonic
C2, Output Cap	1μF, 10V, X7R	GRM319R71A105KC01D	Murata
C3, Boost Cap	0.01µF, 16V, X7R	0805YC103KAT2A	AVX
C4, Feedforward Cap	1μF, 10V, X7R	GRM319R71A105KC01D	Murata
D1, Catch Diode	Schottky, 0.5V at 1A, V <sub>R</sub> = 30V	SS13	Vishay
D2, Boost Diode	Schottky, 0.36V at 15mA	CMDSH-3	Central Semiconductor
L1	4.7μH, 1.6A	SLF6028T-4R7M1R6	TDK
R1	0.2Ω, 0.5W, 1%	WSL2010R2000FEA	Vishay
LED1	1.5A, White LED	LXK2-PW14	Lumileds

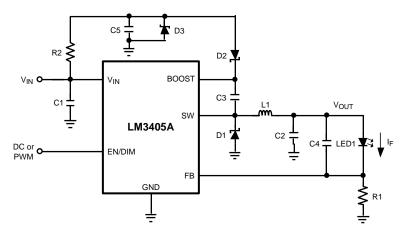


Figure 18.  $V_{BOOST}$  derived from  $V_{IN}$  through a Shunt Zener Diode (D3) (  $V_{IN}$  = 18V,  $I_F$  = 1A )

Table 5. Bill of Materials for Figure 18

Part ID	Part Value	Part Number	Manufacturer
U1	1A LED Driver	LM3405A	National Semiconductor
C1, Input Cap	10μF, 25V, X5R	ECJ-3YB1E106K	Panasonic
C2, Output Cap	1μF, 10V, X7R	GRM319R71A105KC01D	Murata



# Table 5. Bill of Materials for Figure 18 (continued)

Part ID	Part Value	Part Number	Manufacturer
C3, Boost Cap	0.01μF, 16V, X7R	0805YC103KAT2A	AVX
C4, Feedforward Cap	1μF, 10V, X7R	GRM319R71A105KC01D	Murata
C5, Shunt Cap	0.1μF, 16V, X7R	GRM219R71C104KA01D	Murata
D1, Catch Diode	Schottky, 0.5V at 1A, V <sub>R</sub> = 30V	SS13	Vishay
D2, Boost Diode	Schottky, 0.36V at 15mA	CMDSH-3	Central Semiconductor
D3, Zener Diode	4.7V, 350mW, SOT-23	BZX84C4V7	Fairchild
L1	6.8µH, 1.5A	SLF6028T-6R8M1R5	TDK
R1	0.2Ω, 0.5W, 1%	WSL2010R2000FEA	Vishay
R2	1.91kΩ, 1%	CRCW08051K91FKEA	Vishay
LED1	1.5A, White LED	LXK2-PW14	Lumileds

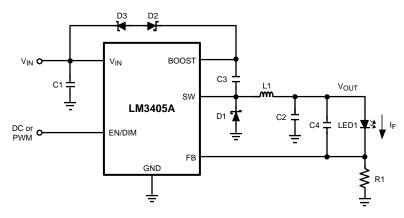


Figure 19.  $V_{BOOST}$  derived from  $V_{IN}$  through a Series Zener Diode (D3) (  $V_{IN}$  = 15V,  $I_F$  = 1A )

# Table 6. Bill of Materials for Figure 19

Part ID	Part Value	Part Number	Manufacturer
U1	1A LED Driver	LM3405A	National Semiconductor
C1, Input Cap	10μF, 25V, X5R	ECJ-3YB1E106K	Panasonic
C2, Output Cap	1μF, 10V, X7R	GRM319R71A105KC01D	Murata
C3, Boost Cap	0.01μF, 16V, X7R	0805YC103KAT2A	AVX
C4, Feedforward Cap	1μF, 10V, X7R	GRM319R71A105KC01D	Murata
D1, Catch Diode	Schottky, 0.5V at 1A, V <sub>R</sub> = 30V	SS13	Vishay
D2, Boost Diode	Schottky, 0.36V at 15mA	CMDSH-3	Central Semiconductor
D3, Zener Diode	11V, 350mW, SOT-23	BZX84C11	Fairchild
L1	6.8µH, 1.5A	SLF6028T-6R8M1R5	TDK
R1	0.2Ω, 0.5W, 1%	WSL2010R2000FEA	Vishay
LED1	1.5A, White LED	LXK2-PW14	Lumileds



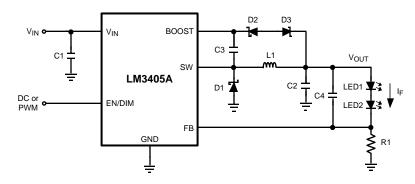


Figure 20.  $V_{BOOST}$  derived from  $V_{OUT}$  through a Series Zener Diode (D3) (  $V_{IN}$  = 18V,  $I_F$  = 1A )

Table 7. Bill of Materials for Figure 20

Part ID	Part Value	Part Number	Manufacturer
U1	1A LED Driver	LM3405A	National Semiconductor
C1, Input Cap	10μF, 25V, X5R	ECJ-3YB1E106K	Panasonic
C2, Output Cap	1μF, 16V, X7R	GRM319R71A105KC01D	Murata
C3, Boost Cap	0.01µF, 16V, X7R	0805YC103KAT2A	AVX
C4, Feedforward Cap	1μF, 16V, X7R	GRM319R71A105KC01D	Murata
D1, Catch Diode	Schottky, 0.5V at 1A, V <sub>R</sub> = 30V	SS13	Vishay
D2, Boost Diode	Schottky, 0.36V at 15mA	CMDSH-3	Central Semiconductor
D3, Zener Diode	3.6V, 350mW, SOT-23	BZX84C3V6	Fairchild
L1	6.8µH, 1.5A	SLF6028T-6R8M1R5	TDK
R1	0.2Ω, 0.5W, 1%	WSL2010R2000FEA	Vishay
LED1	1.5A, White LED	LXK2-PW14	Lumileds
LED2	1.5A, White LED	LXK2-PW14	Lumileds

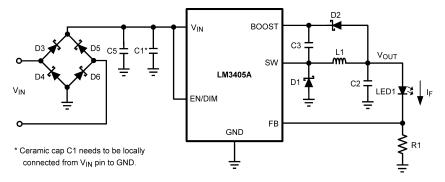


Figure 21. LED MR16 Lamp Application (  $V_{\rm IN}$  = 12V AC,  $I_{\rm F}$  = 0.75A )

Table 8. Bill of Materials for Figure 21

Part ID	Part Value	Part Number	Manufacturer		
U1	1A LED Driver	LM3405A	National Semiconductor		
C1, Input Cap	10μF, 25V, X5R	ECJ-3YB1E106K	Panasonic		
C2, Output Cap	1μF, 10V, X7R	GRM319R71A105KC01D	Murata		
C3, Boost Cap	0.01μF, 16V, X7R	0805YC103KAT2A	AVX		
C5, Input Cap	220μF, 25V, electrolytic	ECE-A1EN221U	Panasonic		



# Table 8. Bill of Materials for Figure 21 (continued)

Part ID	Part Value	Part Number	Manufacturer
D1, Catch Diode	Schottky, 0.5V at 1A, V <sub>R</sub> = 30V	SS13	Vishay
D2, Boost Diode	Schottky, 0.36V at 15mA	CMDSH-3	Central Semiconductor
D3, Rectifier Diode	Schottky, 0.385V at 500mA	CMHSH5-2L	Central Semiconductor
D4, Rectifier Diode	Schottky, 0.385V at 500mA	CMHSH5-2L	Central Semiconductor
D5, Rectifier Diode	Schottky, 0.385V at 500mA	CMHSH5-2L	Central Semiconductor
D6, Rectifier Diode	Schottky, 0.385V at 500mA	CMHSH5-2L	Central Semiconductor
L1	6.8µH, 1.5A	SLF6028T-6R8M1R5	TDK
R1	0.27Ω, 0.33W, 1%	ERJ8BQFR27	Panasonic
LED1	1A, White LED	LXHL-PW09	Lumileds

17-Nov-2012

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty		Lead/Ball Finish		Samples
LM3405AXMK/NOPB	ACTIVE	SOT	DDC	6	1000	Green (RoHS & no Sb/Br)	CU SN	(3) Level-1-260C-UNLIM	(Requires Login)
LM3405AXMKE/NOPB	ACTIVE	SOT	DDC	6	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	
LM3405AXMKX/NOPB	ACTIVE	SOT	DDC	6	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	
LM3405AXMY/NOPB	ACTIVE	MSOP- PowerPAD	DGN	8	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	
LM3405AXMYX/NOPB	ACTIVE	MSOP- PowerPAD	DGN	8	3500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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17-Nov-2012

PACKAGE MATERIALS INFORMATION

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# TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM3405AXMK/NOPB	SOT	DDC	6	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM3405AXMKE/NOPB	SOT	DDC	6	250	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM3405AXMKX/NOPB	SOT	DDC	6	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM3405AXMY/NOPB	MSOP- Power PAD	DGN	8	1000	178.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM3405AXMYX/NOPB	MSOP- Power PAD	DGN	8	3500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

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\*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM3405AXMK/NOPB	SOT	DDC	6	1000	203.0	190.0	41.0
LM3405AXMKE/NOPB	SOT	DDC	6	250	203.0	190.0	41.0
LM3405AXMKX/NOPB	SOT	DDC	6	3000	206.0	191.0	90.0
LM3405AXMY/NOPB	MSOP-PowerPAD	DGN	8	1000	203.0	190.0	41.0
LM3405AXMYX/NOPB	MSOP-PowerPAD	DGN	8	3500	349.0	337.0	45.0

DGN (S-PDSO-G8)

# PowerPAD™ PLASTIC SMALL OUTLINE

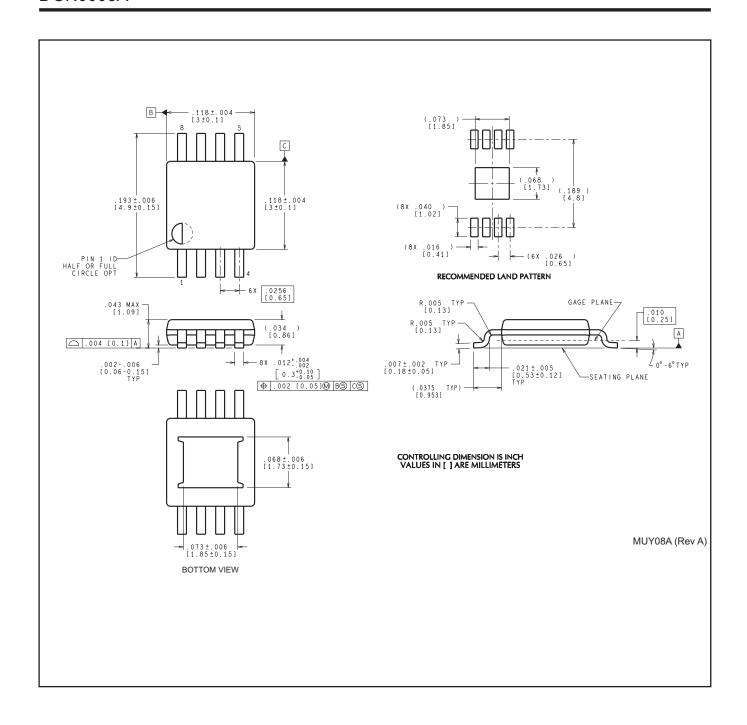


NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="https://www.ti.com">www.ti.com</a>.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO-187 variation AA-T

#### PowerPAD is a trademark of Texas Instruments.





# DDC (R-PDSO-G6)

# PLASTIC SMALL-OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-193 variation AA (6 pin).



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